

# FAN73933

## Half-Bridge Gate Drive IC

### Features

- Floating Channel for Bootstrap Operation to +600V
- Typically 2.5A/2.5A Sourcing/Sinking Current Driving Capability
- Extended Allowable Negative  $V_S$  Swing to -9.8V for Signal Propagation at  $V_{BS}=15V$
- Output in Phase with Input Signal
- 3.3V and 5V Input Logic Compatible
- Matched Propagation Delay for Both Channels
- Built-in UVLO Functions for Both Channels
- Built-in Common-Mode dv/dt Noise Cancelling Circuit
- Programmable Dead-Time Control Function
- Internal 220ns Minimum Dead Time at  $R_{DT}=0\Omega$

### Applications

- High-Speed Power MOSFET and IGBT Gate Driver
- Induction Heating
- High-Power DC-DC Converter
- Synchronous Step-Down Converter
- Motor Drive Inverter

### Description

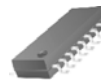
The FAN73933 is a half-bridge, gate-drive IC with programmable dead-time control functions that can drive high-speed MOSFETs and IGBTs operating up to +600V. It has a buffered output stage with all NMOS transistors designed for high-pulse-current driving capability and minimum cross-conduction.

Fairchild's high-voltage process and common-mode noise canceling techniques provide stable operation of the high-side driver under high dv/dt noise circumstances. An advanced level-shift circuit offers high-side gate driver operation up to  $V_S=-9.8V$  (typical) for  $V_{BS}=15V$ .

The UVLO circuit prevents malfunction when  $V_{DD}$  and  $V_{BS}$  are lower than the specified threshold voltage.

The high-current and low-output voltage drop feature makes this device suitable for diverse half- and full-bridge inverters; motor drive inverters, switching mode power supplies, induction heating, and high-power DC-DC converter applications.

14-SOP



### Ordering Information

Part Number	Package	Operating Temperature Range	Eco Status	Packing Method
FAN73933M	14-Lead, Small Outline Integrated Circuit (SOIC), Non-JEDEC, .150 Inch Narrow Body, 225SOP	-40°C to +125°C	RoHS	Tube
FAN73933MX				Tape & Reel



For Fairchild's definition of Eco Status, please visit: [http://www.fairchildsemi.com/company/green/rohs\\_green.html](http://www.fairchildsemi.com/company/green/rohs_green.html).

Typical Application Diagrams

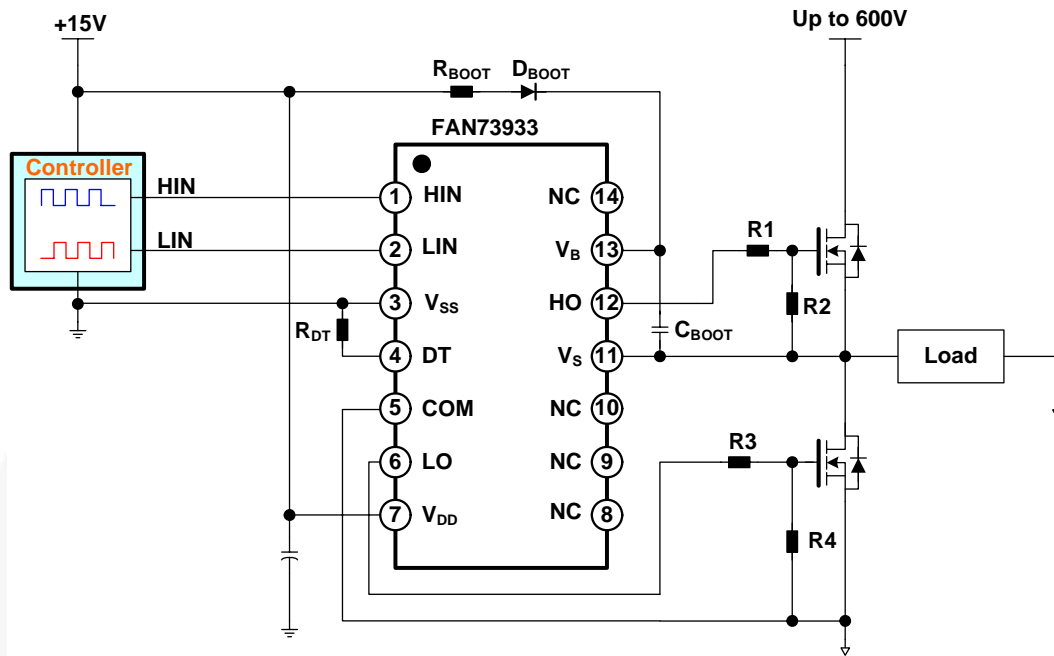


Figure 1. Typical Application Circuit

Internal Block Diagram

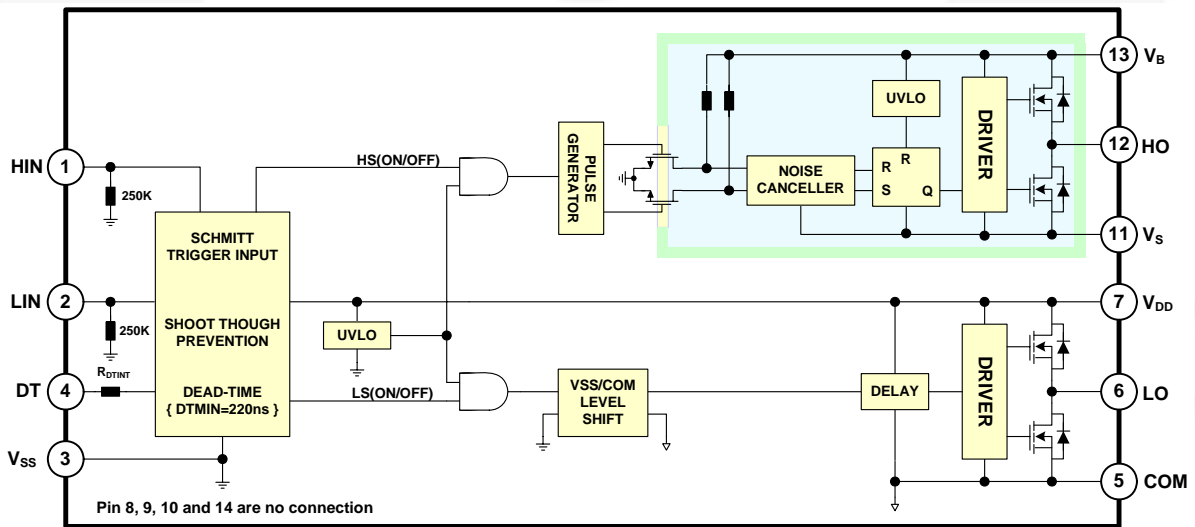


Figure 2. Functional Block Diagram

## Pin Configuration

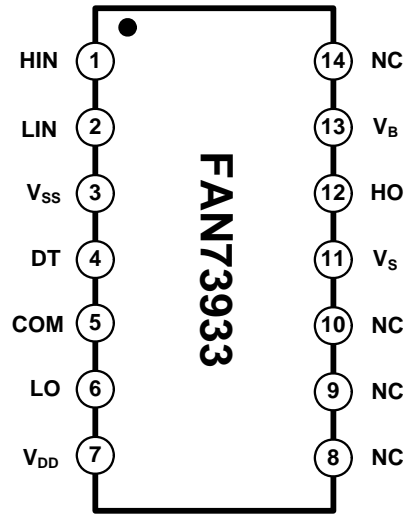


Figure 3. Pin Configurations (Top View)

## Pin Definitions

Pin #	Name	Description
1	HIN	Logic Input for High-Side Gate Driver Output
2	LIN	Logic Input for Low-Side Gate Driver Output
3	$V_{SS}$	Logic Ground
4	DT	Dead-Time Control with External Resistor (Referenced to $V_{SS}$ )
5	COM	Ground
6	LO	Low-Side Driver Return
7	$V_{DD}$	Supply Voltage
8	NC	No Connection
9	NC	No Connection
10	NC	No Connection
11	$V_S$	High-Voltage Floating Supply Return
12	HO	High-Side Driver Output
13	$V_B$	High-Side Floating Supply
14	NC	No Connection

## Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.  $T_A=25^{\circ}\text{C}$  unless otherwise specified.

Symbol	Characteristics	Min.	Max.	Unit
$V_B$	High-Side Floating Supply Voltage	-0.3	625.0	V
$V_S$	High-Side Floating Offset Voltage	$V_B-25.0$	$V_B+0.3$	V
$V_{HO}$	High-Side Floating Output Voltage	$V_S-0.3$	$V_B+0.3$	V
$V_{LO}$	Low-Side Output Voltage	-0.3	$V_{DD}+0.3$	V
$V_{DD}$	Low-Side and Logic Fixed Supply Voltage	-0.3	25.0	V
$V_{IN}$	Logic Input Voltage (HIN and LIN)	-0.3	$V_{DD}+0.3$	V
DT	Programmable Dead-Time Pin Voltage	-0.3	$V_{DD}+0.3$	V
$V_{SS}$	Logic Ground	$V_{DD}-25$	$V_{DD}+0.3$	V
$dV_S/dt$	Allowable Offset Voltage Slew Rate		$\pm 50$	V/ns
$P_D$	Power Dissipation <sup>(1, 2, 3)</sup>		1	W
$\theta_{JA}$	Thermal Resistance		110	$^{\circ}\text{C}/\text{W}$
$T_J$	Junction Temperature		+150	$^{\circ}\text{C}$
$T_{STG}$	Storage Temperature	-55	+150	$^{\circ}\text{C}$

### Notes:

- 1 Mounted on 76.2 x 114.3 x 1.6mm PCB (FR-4 glass epoxy material).
- 2 Refer to the following standards:  
JESD51-2: Integral circuits thermal test method environmental conditions - natural convection, and  
JESD51-3: Low effective thermal conductivity test board for leaded surface mount packages.
- 3 Do not exceed maximum  $P_D$  under any circumstances.

## Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Min.	Max.	Unit
$V_B$	High-Side Floating Supply Voltage	$V_S+10$	$V_S+20$	V
$V_S$	High-Side Floating Supply Offset Voltage	$6-V_{DD}$	600	V
$V_{HO}$	High-Side Output Voltage	$V_S$	$V_B$	V
$V_{DD}$	Low-Side and Logic Fixed Supply Voltage	10	20	V
$V_{LO}$	Low-Side Output Voltage	COM	$V_{DD}$	V
$V_{IN}$	Logic Input Voltage (HIN and LIN)	$V_{SS}$	$V_{DD}$	V
DT	Programmable Dead-Time Pin Voltage	$V_{SS}$	$V_{DD}$	V
$V_{SS}$	Logic Ground	-5	+5	V
$T_A$	Operating Ambient Temperature	-40	+125	$^{\circ}\text{C}$

## Electrical Characteristics

$V_{BIAS}(V_{DD}, V_{BS})=15.0V$ ,  $V_{SS}=COM=0V$ ,  $DT=V_{SS}$  and  $T_A = 25^\circ C$ , unless otherwise specified. The  $V_{IN}$  and  $I_{IN}$  parameters are referenced to  $V_{SS}/COM$  and are applicable to the respective input leads: HIN and LIN. The  $V_O$  and  $I_O$  parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Characteristics	Test Condition	Min.	Typ.	Max.	Unit
<b>POWER SUPPLY SECTION</b>						
$I_{QDD}$	Quiescent $V_{DD}$ Supply Current	$V_{IN}=0V$ or $5V$		0.9	1.5	mA
$I_{QBS}$	Quiescent $V_{BS}$ Supply Current	$V_{IN}=0V$ or $5V$		50	100	$\mu A$
$I_{PDD}$	Operating $V_{DD}$ Supply Current	$f_{IN}=20KHz$ , No Load		1.3	1.9	mA
$I_{PBS}$	Operating $V_{BS}$ Supply Current	$C_L=1nF$ , $f_{IN}=20KHz$ , rms		450	800	$\mu A$
$I_{LK}$	Offset Supply Leakage Current	$V_B=V_S=600V$			10	$\mu A$
<b>BOOTSTRAPPED SUPPLY SECTION</b>						
$V_{DDUV+}$ $V_{BSUV+}$	$V_{DD}$ and $V_{BS}$ Supply Under-Voltage Positive-Going Threshold Voltage	$V_{IN}=0V$ , $V_{DD}=V_{BS}=Sweep$	8.0	9.0	10	V
$V_{DDUV-}$ $V_{BSUV-}$	$V_{DD}$ and $V_{BS}$ Supply Under-Voltage Negative-Going Threshold Voltage	$V_{IN}=0V$ , $V_{DD}=V_{BS}=Sweep$	7.4	8.4	9.4	V
$V_{DDUVH-}$ $V_{BSUVH}$	$V_{DD}$ and $V_{BS}$ Supply Under-Voltage Lockout Hysteresis Voltage	$V_{IN}=0V$ , $V_{DD}=V_{BS}=Sweep$		0.6		V
<b>INPUT LOGIC SECTION</b>						
$V_{IH}$	Logic "1" Input Voltage for HO & Logic "0" for LO		2.5			V
$V_{IL}$	Logic "0" Input Voltage for HO & Logic "1" for LO				0.8	V
$I_{IN+}$	Logic Input High Bias Current	$V_{IN}=5V$		20	50	$\mu A$
$I_{IN-}$	Logic Input Low Bias Current	$V_{IN}=0V$			2	$\mu A$
$R_{IN}$	Logic Input Pull-Down Resistance		100	250		$K\Omega$
<b>GATE DRIVER OUTPUT SECTION</b>						
$V_{OH}$	High-Level Output Voltage ( $V_{BIAS} - V_O$ )	No Load			1.5	V
$V_{OL}$	Low-Level Output Voltage	No Load			100	mV
$I_{O+}$	Output High, Short-Circuit Pulsed Current <sup>(4)</sup>	$V_{HO}=0V$ , $V_{IN}=5V$ , $PW \leq 10\mu s$	2.0	2.5		A
$I_{O-}$	Output Low, Short-Circuit Pulsed Current <sup>(4)</sup>	$V_{HO}=15V$ , $V_{IN}=0V$ , $PW \leq 10\mu s$	2.0	2.5		A
$V_S$	Allowable Negative $V_S$ Pin Voltage for IN Signal Propagation to HO			-9.8	-7.0	V

### Note:

- These parameters guaranteed by design.

## Dynamic Electrical Characteristics

$V_{BIAS}(V_{DD}, V_{BS})=15.0V$ ,  $V_{SS}=COM=0V$ ,  $C_L=1000pF$ ,  $DT=V_{SS}$  and  $T_A=25^\circ C$ , unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$t_{ON}$	Turn-On Propagation Delay Time <sup>(5)</sup>	$V_S=0V$ , $R_{DT}=0\Omega$		160	230	ns
$t_{OFF}$	Turn-Off Propagation Delay Time	$V_S=0V$		160	230	ns
$Mt_{ON}$	Delay Matching, HO & LO Turn-On			0	50	ns
$Mt_{OFF}$	Delay Matching, HO & LO Turn-Off			0	50	ns
$t_R$	Turn-On Rise Time	$V_S=0V$		40	60	ns
$t_F$	Turn-Off Fall Time	$V_S=0V$		20	35	ns
DT	Dead Time: LO Turn-Off to HO Turn-On & HO Turn-Off to LO Turn-On	$R_{DT}=0\Omega$	170	220	270	ns
		$R_{DT}=300K\Omega$	400	500	600	ns
MDT	Dead-Time Matching= $ DT_{LO-HO} - DT_{HO-LO} $	$R_{DT}=0\Omega$		0	50	ns
		$R_{DT}=300K\Omega$		0	100	ns

### Note:

5 The turn-on propagation display does not include dead time.

## Typical Characteristics

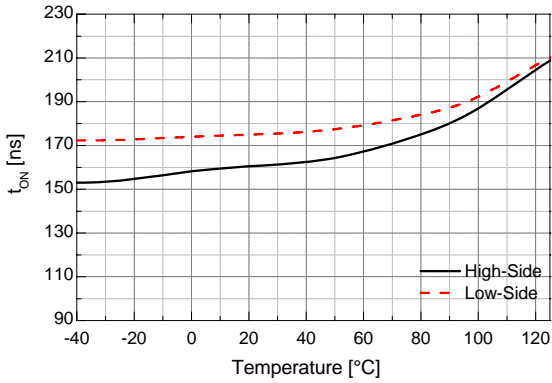


Figure 4. Turn-On Propagation Delay vs. Temperature

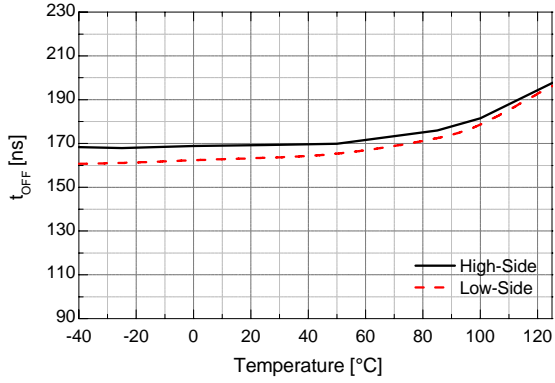


Figure 5. Turn-Off Propagation Delay vs. Temperature

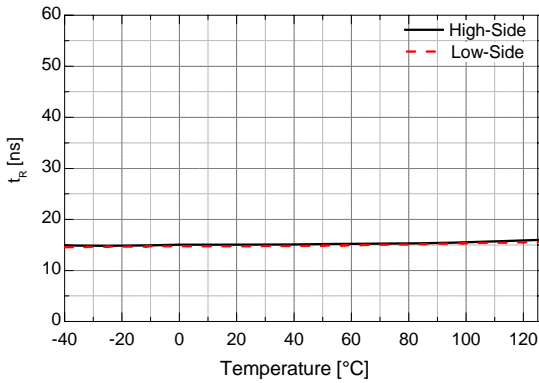


Figure 6. Turn-On Rise Time vs. Temperature

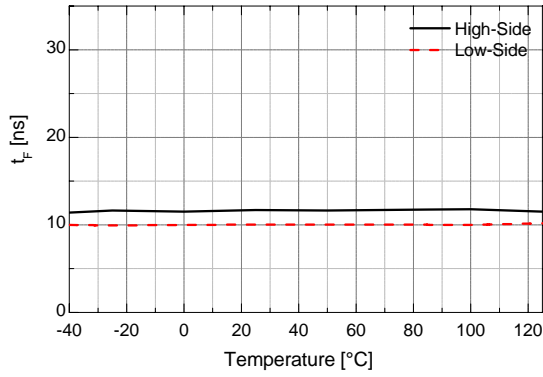


Figure 7. Turn-Off Fall Time vs. Temperature

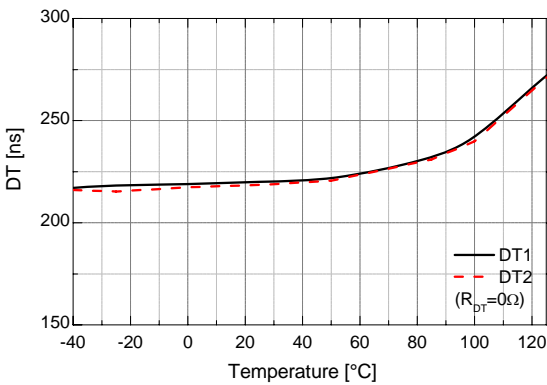


Figure 8. Dead Time ( $R_{DT}=0\Omega$ ) vs. Temperature

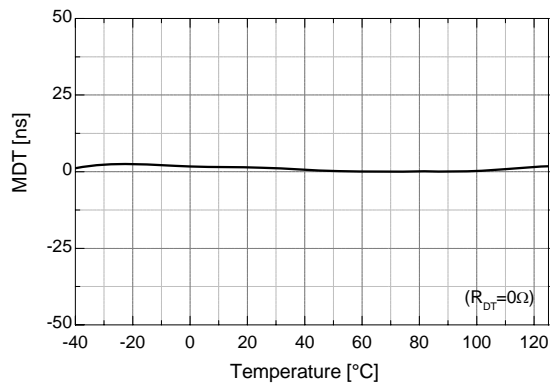


Figure 9. Dead Time Matching ( $R_{DT}=0\Omega$ ) vs. Temperature

Typical Characteristics (Continued)

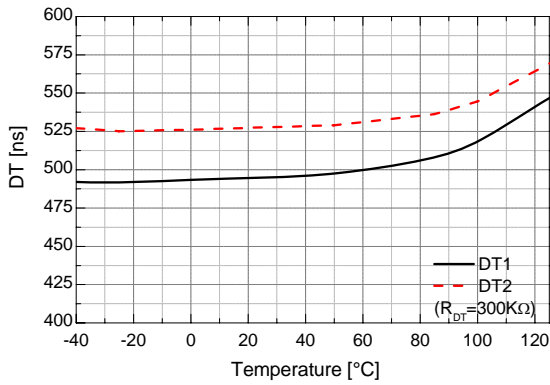


Figure 10. Dead Time ( $R_{DT}=300K\Omega$ ) vs. Temperature

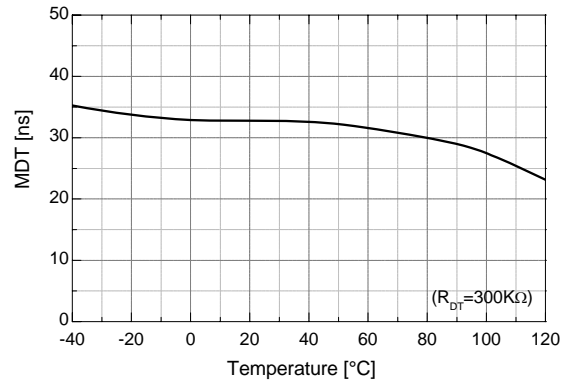


Figure 11. Dead Time Matching ( $R_{DT}=300K\Omega$ ) vs. Temperature

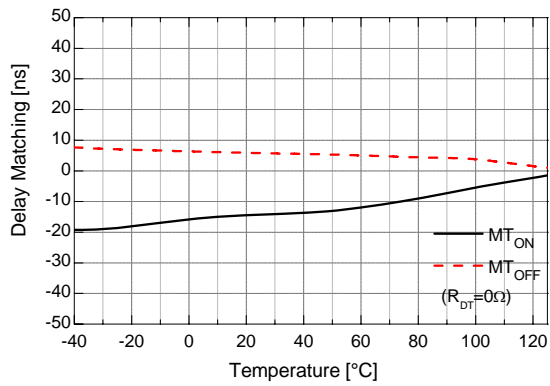


Figure 12. Delay Matching vs. Temperature

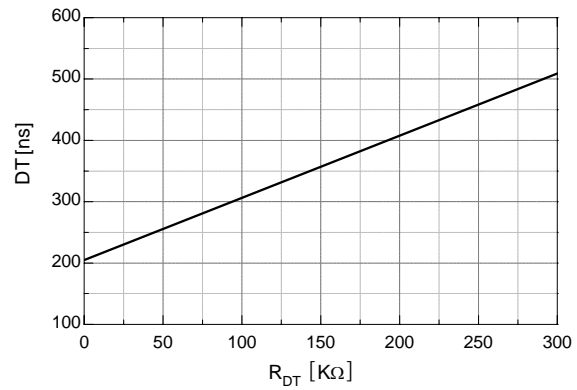


Figure 13. Dead Time vs.  $R_{DT}$

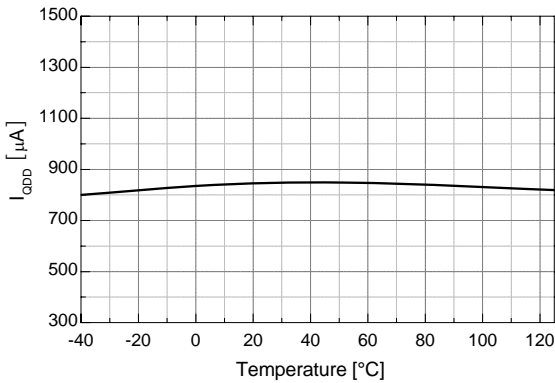


Figure 14. Quiescent  $V_{DD}$  Supply Current vs. Temperature

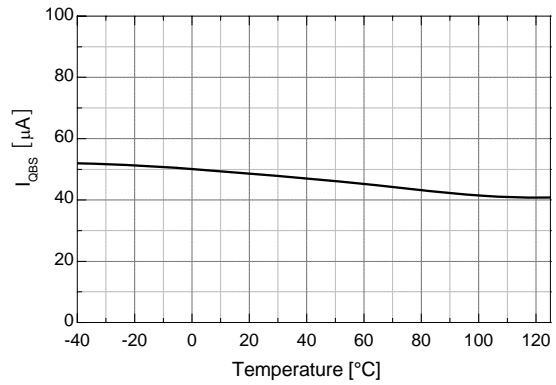


Figure 15. Quiescent  $V_{BS}$  Supply Current vs. Temperature



Typical Characteristics (Continued)

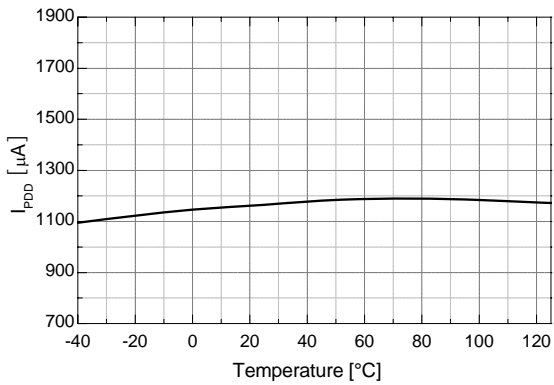


Figure 16. Operating  $V_{CC}$  Supply Current vs. Temperature

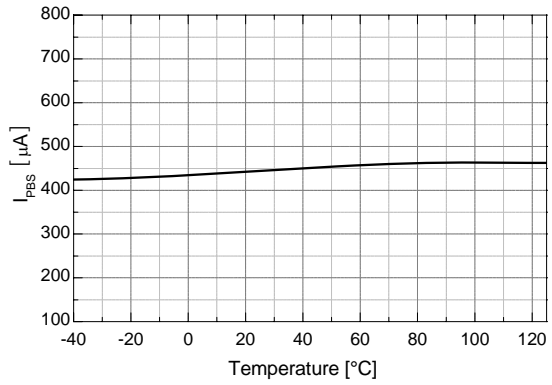


Figure 17. Operating  $V_{BS}$  Supply Current vs. Temperature

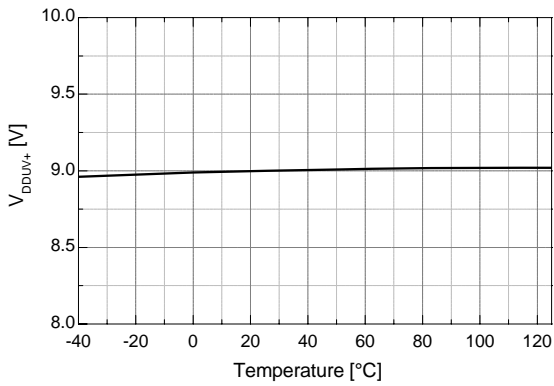


Figure 18.  $V_{DD}$  UVLO+ vs. Temperature

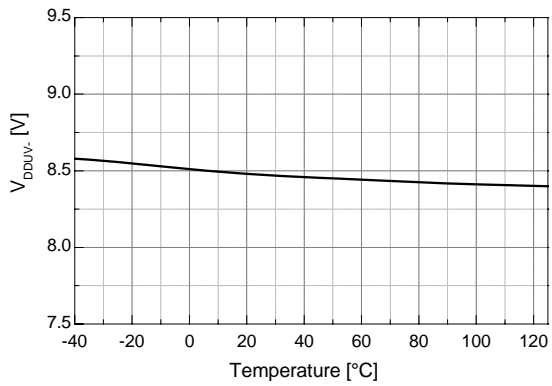


Figure 19.  $V_{DD}$  UVLO- vs. Temperature

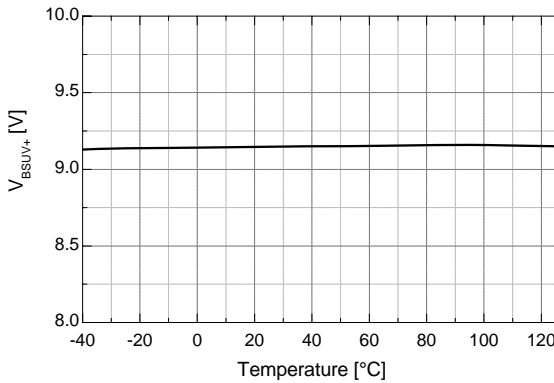


Figure 20.  $V_{BS}$  UVLO+ vs. Temperature

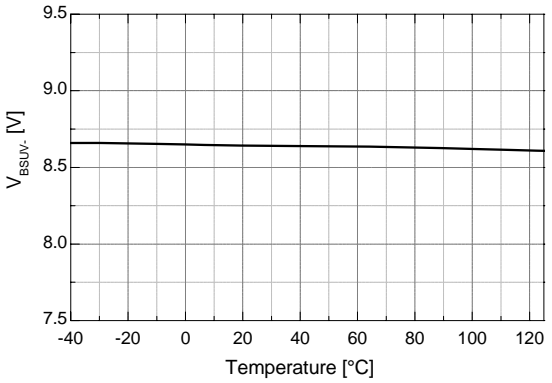


Figure 21.  $V_{BS}$  UVLO- vs. Temperature

Typical Characteristics (Continued)

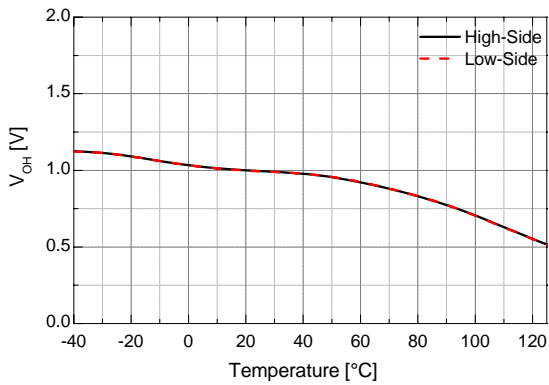


Figure 22. High-Level Output Voltage vs. Temperature

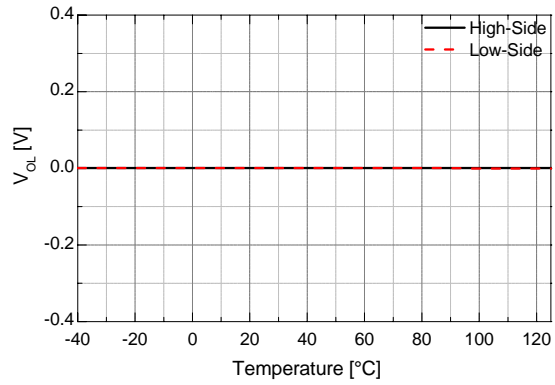


Figure 23. Low-Level Output Voltage vs. Temperature

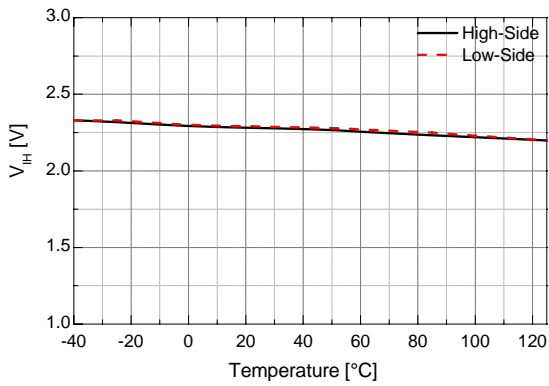


Figure 24. Logic High Input Voltage vs. Temperature

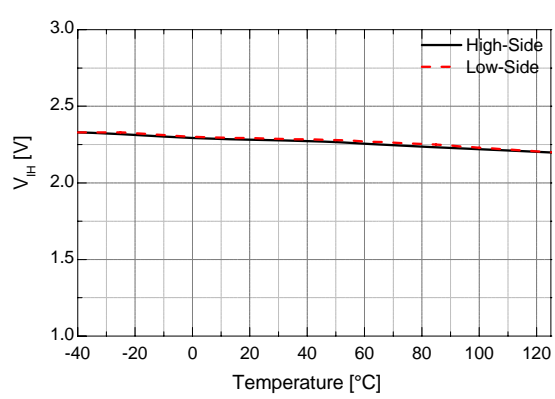


Figure 25. Logic Low Input Voltage vs. Temperature

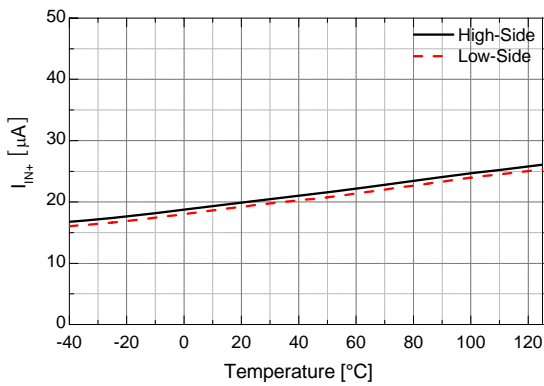


Figure 26. Logic Input High Bias Current vs. Temperature

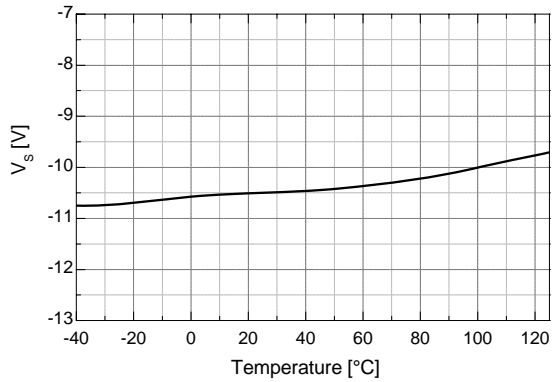


Figure 27. Allowable Negative  $V_S$  Voltage vs. Temperature

Typical Characteristics (Continued)

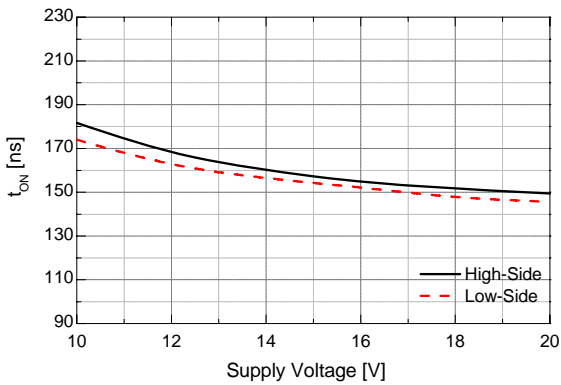


Figure 28. Turn-On Propagation Delay vs. Supply Voltage

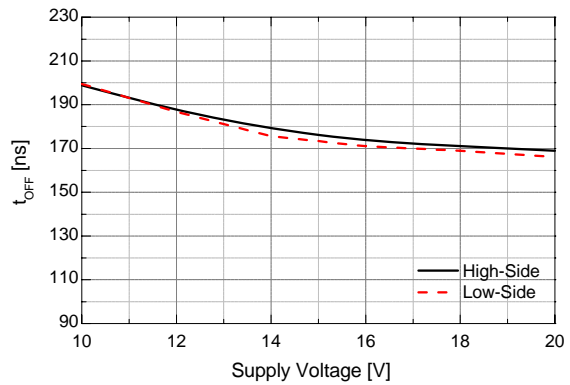


Figure 29. Turn-Off Propagation Delay vs. Supply Voltage

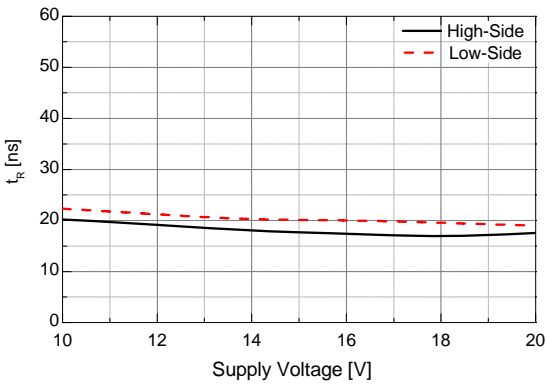


Figure 30. Turn-On Rise Time vs. Supply Voltage

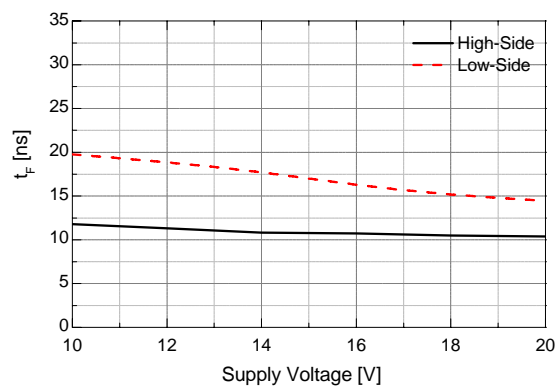


Figure 31. Turn-Off Fall Time vs. Supply Voltage

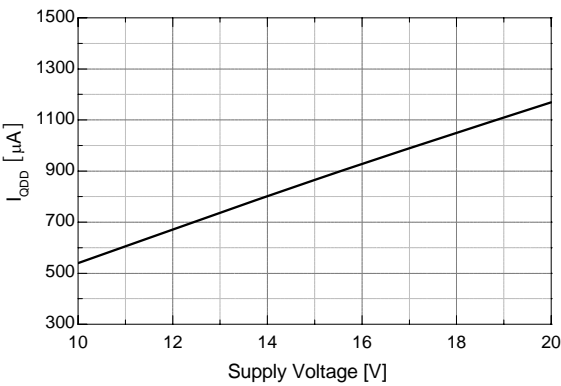


Figure 32. Quiescent  $V_{DD}$  Supply Current vs. Supply Voltage

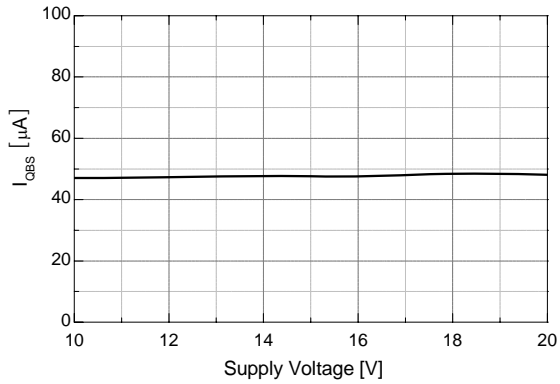


Figure 33. Quiescent  $V_{BS}$  Supply Current vs. Supply Voltage

Typical Characteristics (Continued)

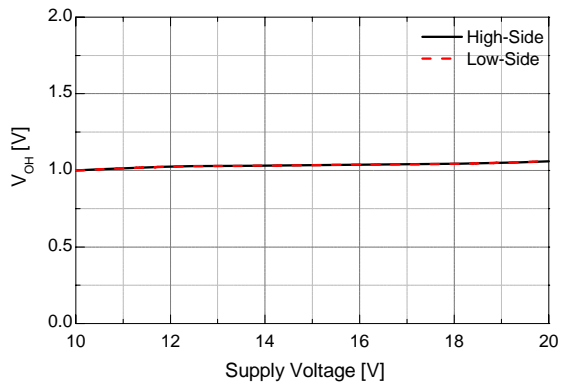


Figure 34. High-Level Output Voltage vs. Supply Voltage

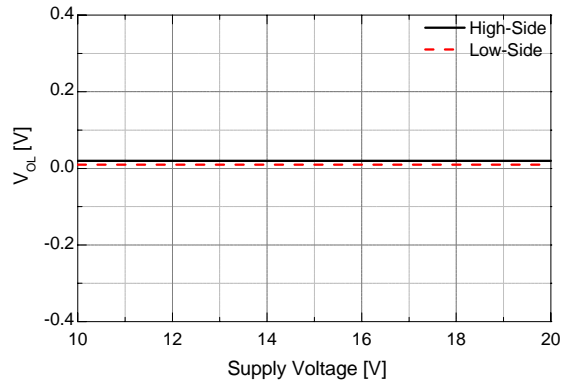


Figure 35. Low-Level Output Voltage vs. Supply Voltage

### Switching Time Definitions

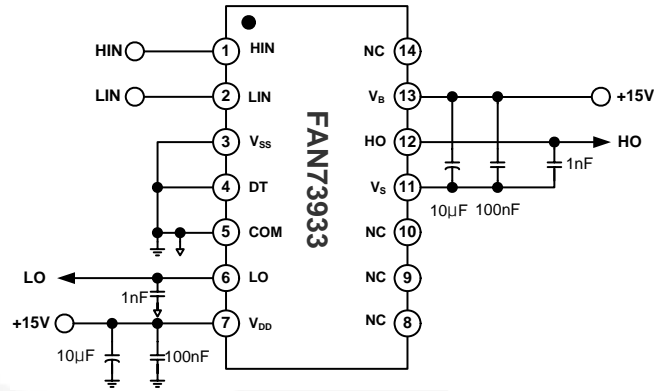


Figure 36. Switching Time Test Circuit

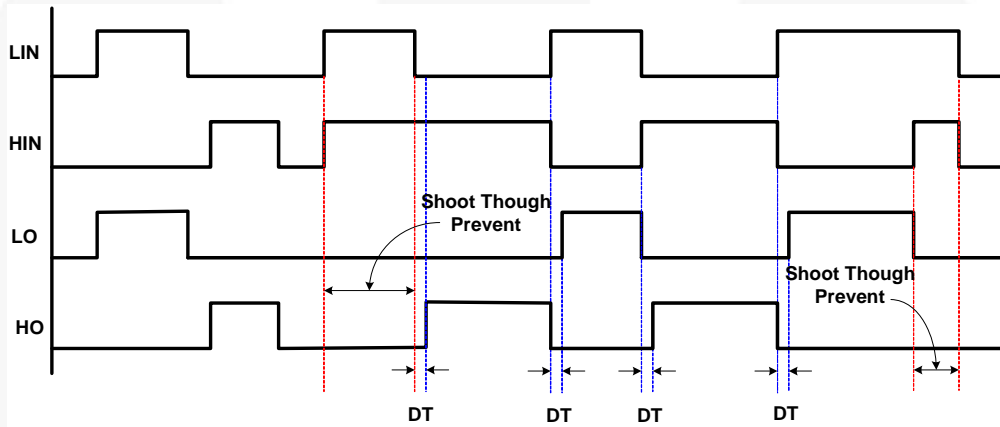


Figure 37. Input/Output Timing Diagram

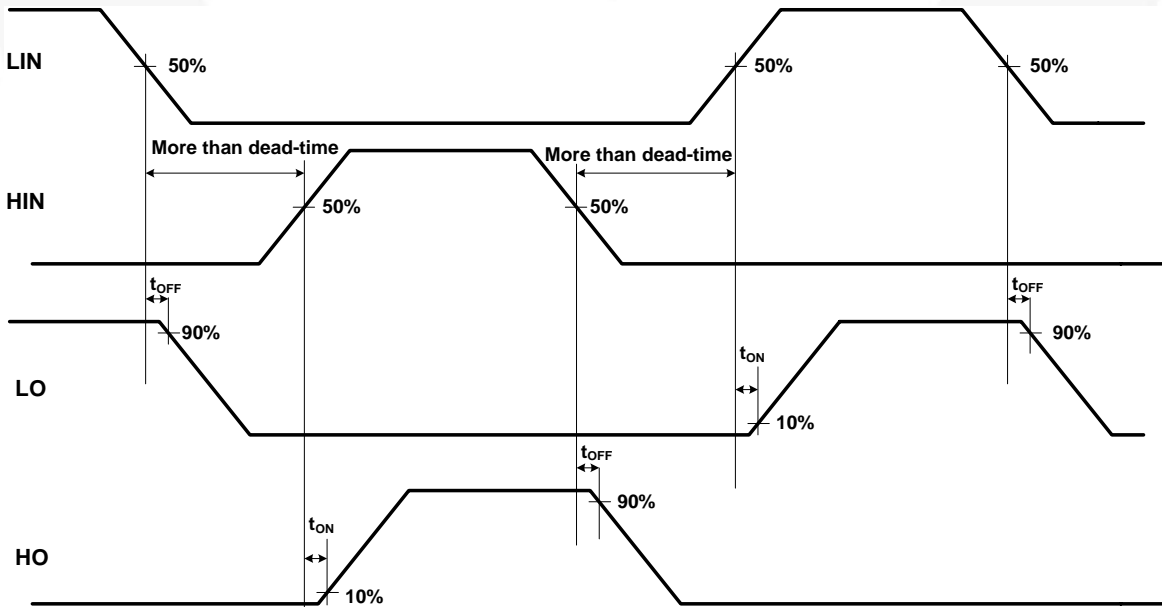


Figure 38. Switching Time Waveform Definitions

## Application Information

### Negative $V_S$ Transient

The bootstrap circuit has the advantage of being simple and low cost, but has some limitations. The biggest difficulty with this circuit is the negative voltage present at the emitter of the high-side switching device when the high-side switch is turned off in half-bridge applications.

If the high-side switch, Q1, turns-off while the load current is flowing to an inductive load; a current commutation occurs from high-side switch, Q1, to the diode, D2, in parallel with the low-side switch of the same inverter leg. Then the negative voltage present at the emitter of the high-side switching device, just before the freewheeling diode, D2, starts clamping, causes load current to suddenly flow to the low-side freewheeling diode, D2, as shown in Figure 39.

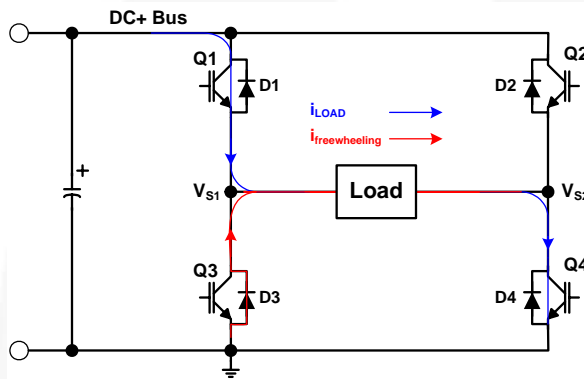


Figure 39. Half-Bridge Application Circuits

This negative voltage can be trouble for the gate driver's output stage. There is the possibility to develop an over-voltage condition of the bootstrap capacitor, input signal missing, and latch-up problems because it directly affects the source  $V_S$  pin of the gate driver, as shown in Figure 40. This undershoot voltage is called "negative  $V_S$  transient".

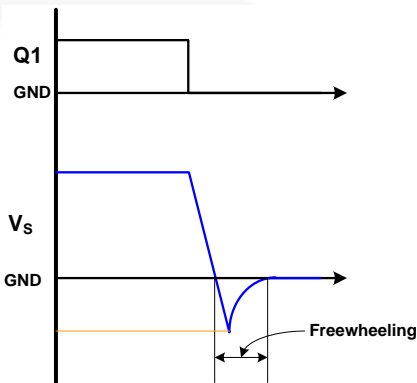


Figure 40.  $V_S$  Waveforms During Q1 Turn-Off

Figure 41. and Figure 42. show the commutation of the load current between the high-side switch, Q1, and low-side freewheeling diode, D3, in same inverter leg. The parasitic inductances in the inverter circuit from the die wire bonding to the PCB tracks are jumped together in  $L_C$  and  $L_E$  for each IGBT. When the high-side switch, Q1, and low-side switch, Q4, are turned on; the  $V_{S1}$  node is below DC+ voltage by the voltage drops associated with the power switch and the parasitic inductances of the circuit due to load current is flows from Q1 and Q4, as shown in Figure 41. When the high-side switch, Q1, is turned off and Q4 remains turned on, the load current to flows the low-side freewheeling diode, D3, due to the inductive load connected to  $V_{S1}$  as shown in Figure 42. The current flows from ground (which is connected to the COM pin of the gate driver) to the load and the negative voltage present at the emitter of the high-side switching device.

In this case, the COM pin of the gate driver is at a higher potential than the  $V_S$  pin due to the voltage drops associated with freewheeling diode, D3, and parasitic elements,  $L_{C3}$  and  $L_{E3}$ .

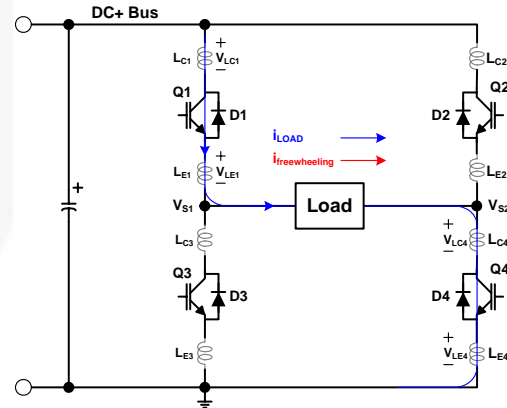


Figure 41. Q1 and Q4 Turn-On

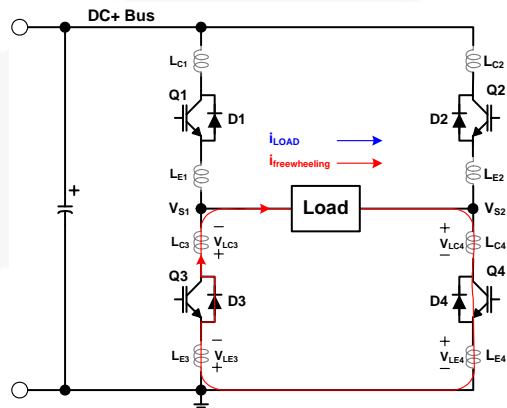
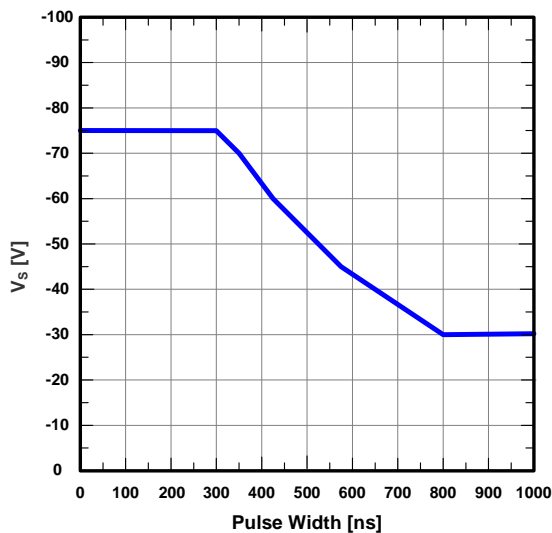


Figure 42. Q1 Turn-Off and D3 Conducting

The FAN73933 has a negative  $V_S$  transient performance curve, as shown in Figure 43.



**Figure 43. Negative  $V_S$  Transient Characteristic**

Even though the FAN73933 has been shown able to handle these negative  $V_S$  transient conditions, it is strongly recommended that the circuit designer limit the negative  $V_S$  transient as much as possible by careful PCB layout to minimize the value of parasitic elements and component use. The amplitude of negative  $V_S$  voltage is proportional to the parasitic inductances and the turn-off speed,  $di/dt$ , of the switching device.

## General Guidelines

### Printed Circuit Board Layout

The layout recommended for minimized parasitic elements is as follows:

- Direct tracks between switches with no loops or deviation.
- Avoid interconnect links. These can add significant inductance.
- Reduce the effect of lead-inductance by lowering package height above the PCB.
- Consider co-locating both power switches to reduce track length.
- To minimize noise coupling, the ground plane should not be placed under or near the high-voltage floating side.
- To reduce the EM coupling and improve the power switch turn-on/off performance, the gate drive loops must be reduced as much as possible.

## Placement of Components

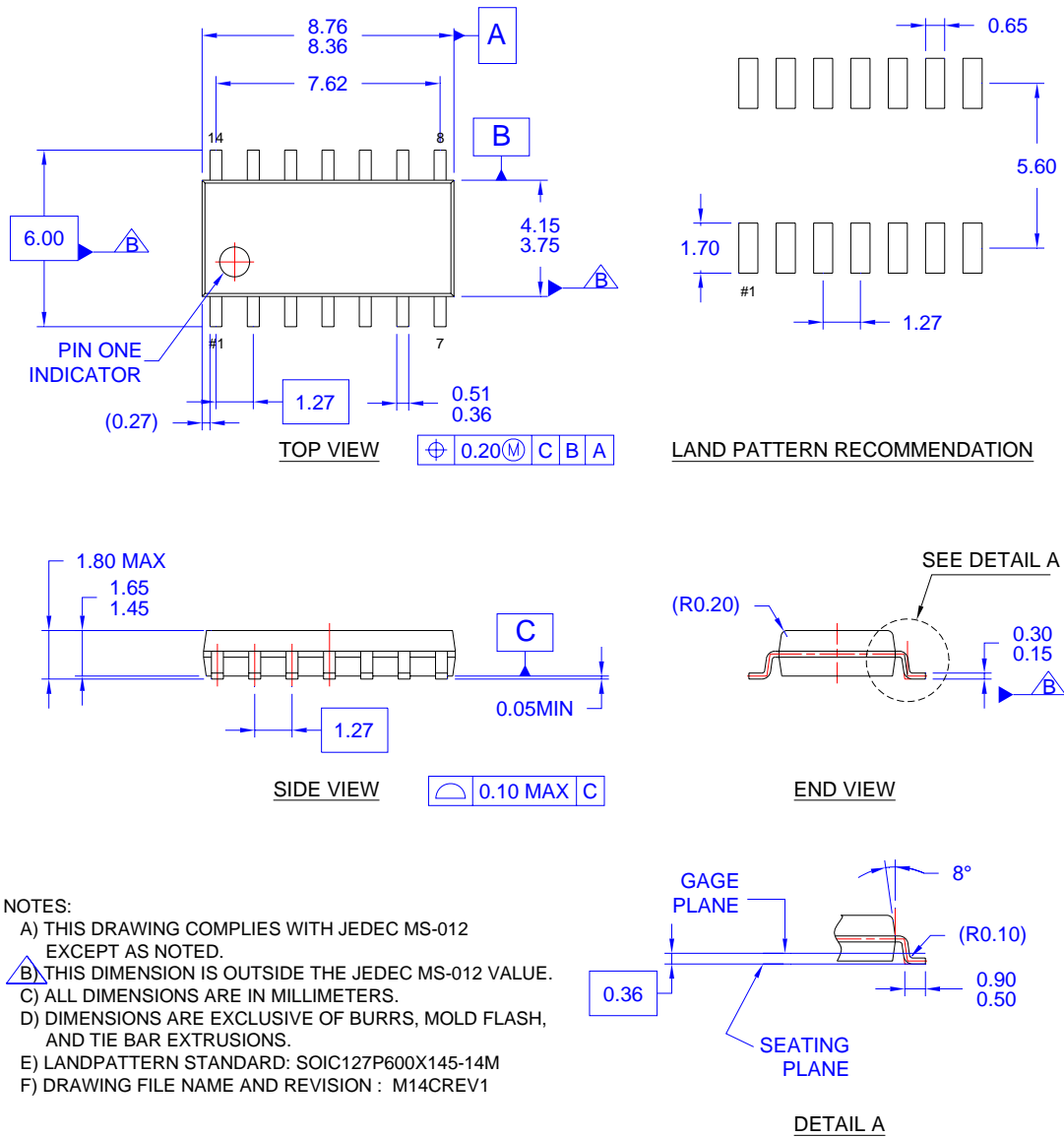
The recommended selection of component is as follows:

- Place a bypass capacitor between the  $V_{DD}$  and  $V_{SS}$  pins. A ceramic  $1\mu\text{F}$  capacitor is suitable for most applications. This component should be placed as close as possible to the pins to reduce parasitic elements.
- The bypass capacitor from  $V_{CC}$  to COM supports both the low-side driver and bootstrap capacitor recharge. A value at least ten times higher than the bootstrap capacitor is recommended.
- The bootstrap resistor,  $R_{BOOT}$ , must be considered in sizing the bootstrap resistance and the current developed during initial bootstrap charge. If the resistor is needed in series with the bootstrap diode, verify that  $V_B$  does not fall below COM (ground). Recommended use is typically  $5 \sim 10\Omega$ , which increases the  $V_{BS}$  time constant. If the voltage drop of the bootstrap resistor and diode is too high or the circuit topology does not allow a sufficient charging time, a fast recovery or ultra-fast recovery diode can be used.
- The bootstrap capacitor,  $C_{BOOT}$ , uses a low-ESR capacitor, such as a ceramic capacitor.

It is strongly recommended that the placement of components is as follows:

- Place components tied to the floating voltage pins ( $V_B$  and  $V_S$ ) near the respective high-voltage portions of the device and the FAN73933. NC (not connected) pins in this package maximize the distance between the high-voltage and low-voltage pins (see Figure 3).
- Place and route for bypass capacitors and gate resistors as close as possible to gate drive IC.
- Locate the bootstrap diode,  $D_{BOOT}$ , as close as possible to bootstrap capacitor,  $C_{BOOT}$ .
- The bootstrap diode must use a lower forward voltage drop and minimal switching time as soon as possible for fast recovery or ultra-fast diode.

### Physical Dimensions



**Figure 44. 14-Lead, Small Outline Integrated Circuit (SOIC), Non-JEDEC, .150 Inch Narrow Body, 225SOP**

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